

74HC165; 74HCT165

8-bit parallel-in/serial out shift register

Product data sheet

1. General description

The 74HC165; 74HCT165 are high-speed Si-gate CMOS devices that comply with JEDEC standard no. 7A. They are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC165; 74HCT165 are 8-bit parallel-load or serial-in shift registers with complementary serial outputs (Q_7 and $\overline{Q_7}$) available from the last stage. When the parallel load (\overline{PL}) input is LOW, parallel data from the D0 to D7 inputs are loaded into the register asynchronously.

When \overline{PL} is HIGH, data enters the register serially at the DS input and shifts one place to the right ($Q_0 \rightarrow Q_1 \rightarrow Q_2$, etc.) with each positive-going clock transition. This feature allows parallel-to-serial converter expansion by tying the Q_7 output to the DS input of the succeeding stage.

The clock input is a gated-OR structure which allows one input to be used as an active LOW clock enable (\overline{CE}) input. The pin assignment for the CP and \overline{CE} inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of input \overline{CE} should only take place while CP HIGH for predictable operation. Either the CP or the \overline{CE} should be HIGH before the LOW-to-HIGH transition of \overline{PL} to prevent shifting the data when \overline{PL} is activated.

2. Features

- Asynchronous 8-bit parallel load
- Synchronous serial input
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Applications

- Parallel-to-serial data conversion

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC165N 74HCT165N	-40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HC165D 74HCT165D	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC165DB 74HCT165DB	-40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HC165PW 74HCT165PW	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC165BQ 74HCT165BQ	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

5. Functional diagram

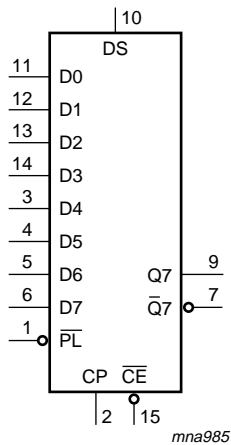


Fig 1. Logic symbol

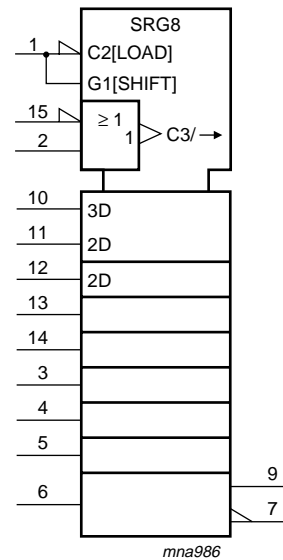


Fig 2. IEC logic symbol

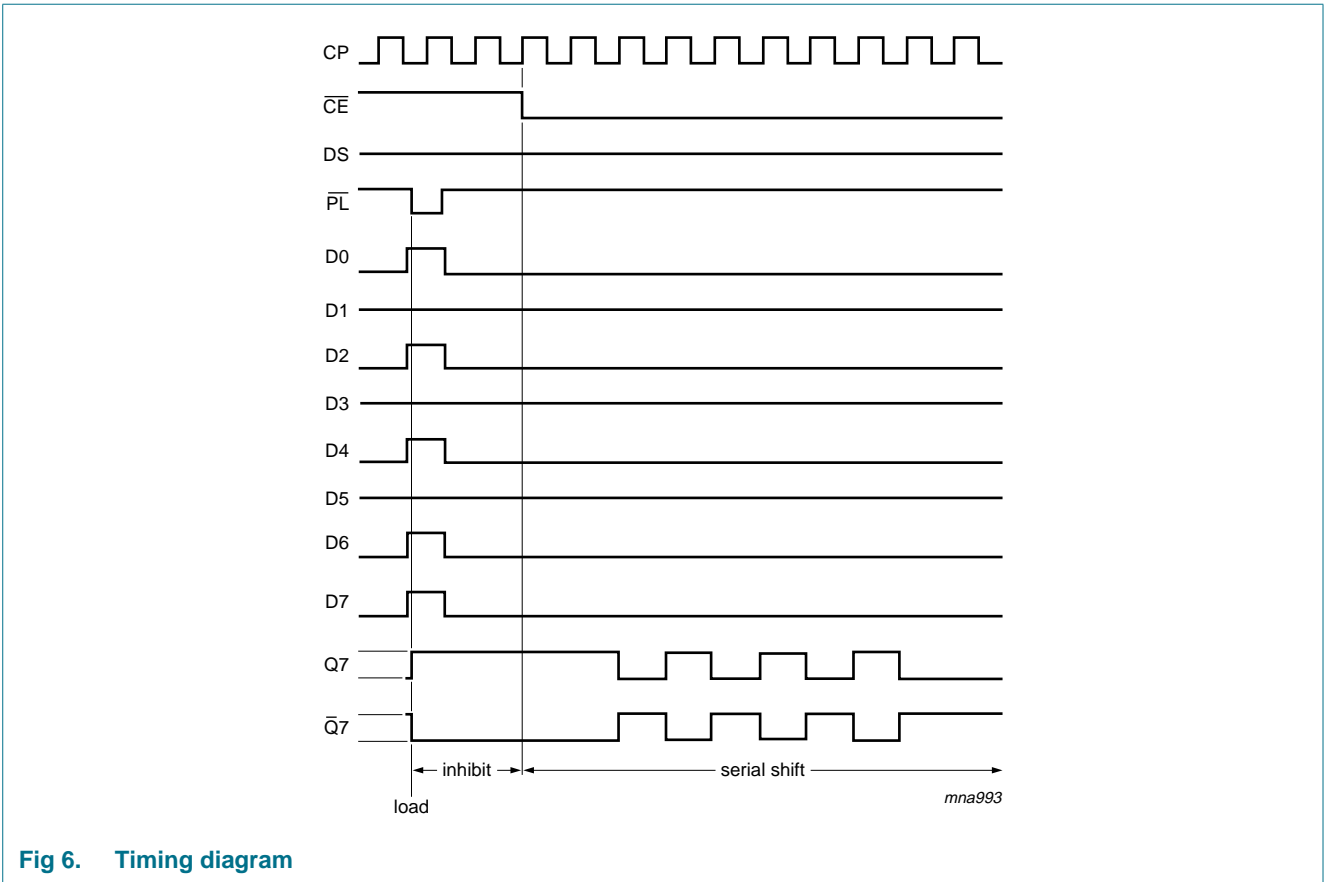


Fig 6. Timing diagram

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	±25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	Min	Max	Unit	
P _{tot}	total power dissipation	T _{amb} = -40 °C to +125 °C				
		DIP16 package	[2]	-	750	mW
		SO16 package	[3]	-	500	mW
		(T)SSOP16 package	[4]	-	500	mW
		DHVQFN16 package	[5]	-	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC165			74HCT165			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC165										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = -4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = -5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT165										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V								
		Dn and DS inputs	-	35	126	-	157.5	-	171.5	μA
		CP \overline{CE} , and \overline{PL} inputs	-	65	234	-	292.5	-	318.5	μA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 12](#)

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC165										
t_{pd}	propagation delay	CP or \overline{CE} to Q7, $\overline{Q7}$; see Figure 7	[1]							
		$V_{CC} = 2.0$ V	-	52	165	-	205	-	250	ns
		$V_{CC} = 4.5$ V	-	19	33	-	41	-	50	ns
		$V_{CC} = 6.0$ V	-	15	28	-	35	-	43	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	16	-	-	-	-	-	ns
		\overline{PL} to Q7, $\overline{Q7}$; see Figure 8								
		$V_{CC} = 2.0$ V	-	50	165	-	205	-	250	ns
		$V_{CC} = 4.5$ V	-	18	33	-	41	-	50	ns
		$V_{CC} = 6.0$ V	-	14	28	-	35	-	43	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	15	-	-	-	-	-	ns
		D7 to Q7, $\overline{Q7}$; see Figure 9								
		$V_{CC} = 2.0$ V	-	36	120	-	150	-	180	ns
		$V_{CC} = 4.5$ V	-	13	24	-	30	-	36	ns
		$V_{CC} = 6.0$ V	-	10	20	-	26	-	31	ns
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	11	-	-	-	-	-	ns
		t_t	transition time	Q7, $\overline{Q7}$ output; see Figure 7	[2]					
$V_{CC} = 2.0$ V	-			19	75	-	95	-	110	ns
$V_{CC} = 4.5$ V	-			7	15	-	19	-	22	ns
$V_{CC} = 6.0$ V	-			6	13	-	16	-	19	ns
t_w	pulse width	CP input HIGH or LOW; see Figure 7								
		$V_{CC} = 2.0$ V	80	17	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	6	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	5	-	17	-	20	-	ns
		\overline{PL} input LOW; see Figure 8								
		$V_{CC} = 2.0$ V	80	14	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	5	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	4	-	17	-	20	-	ns
t_{rec}	recovery time	\overline{PL} to CP, \overline{CE} ; see Figure 8								
		$V_{CC} = 2.0$ V	100	22	-	125	-	150	-	ns
		$V_{CC} = 4.5$ V	20	8	-	25	-	30	-	ns
		$V_{CC} = 6.0$ V	17	6	-	21	-	26	-	ns

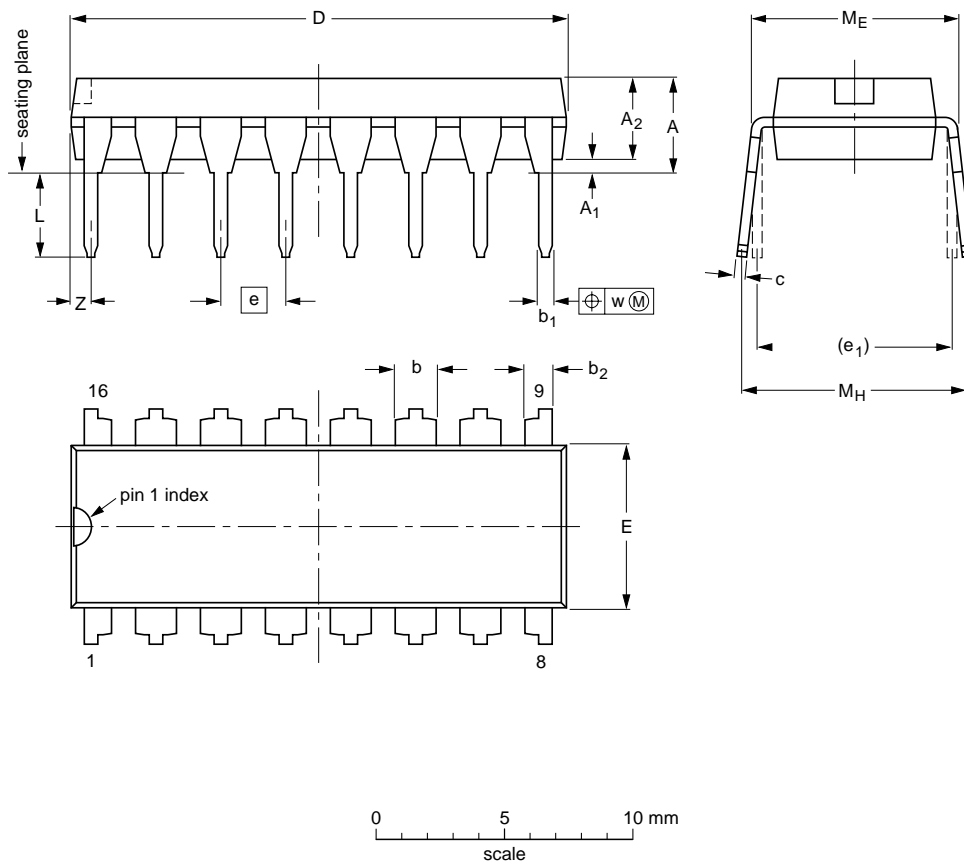
Table 7. Dynamic characteristics ...continued
 GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 12](#)

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Typ	Max	Min	Max	Min	Max		
t_{su}	set-up time	DS to CP, \overline{CE} ; see Figure 10									
		$V_{CC} = 2.0$ V	80	11	-	100	-	120	-	ns	
		$V_{CC} = 4.5$ V	16	4	-	20	-	24	-	ns	
		$V_{CC} = 6.0$ V	14	3	-	17	-	20	-	ns	
		\overline{CE} to CP and CP to \overline{CE} ; see Figure 10									
		$V_{CC} = 2.0$ V	80	17	-	100	-	120	-	ns	
		$V_{CC} = 4.5$ V	16	6	-	20	-	24	-	ns	
		$V_{CC} = 6.0$ V	14	5	-	17	-	20	-	ns	
		Dn to \overline{PL} ; see Figure 11									
		$V_{CC} = 2.0$ V	80	22	-	100	-	120	-	ns	
		$V_{CC} = 4.5$ V	16	8	-	20	-	24	-	ns	
		$V_{CC} = 6.0$ V	14	6	-	17	-	20	-	ns	
t_h	hold time	DS to CP, \overline{CE} and Dn to \overline{PL} ; see Figure 10									
		$V_{CC} = 2.0$ V	5	6	-	5	-	5	-	ns	
		$V_{CC} = 4.5$ V	5	2	-	5	-	5	-	ns	
		$V_{CC} = 6.0$ V	5	2	-	5	-	5	-	ns	
		\overline{CE} to CP and CP to \overline{CE} ; see Figure 10									
		$V_{CC} = 2.0$ V	5	-17	-	5	-	5	-	ns	
		$V_{CC} = 4.5$ V	5	-6	-	5	-	5	-	ns	
		$V_{CC} = 6.0$ V	5	-5	-	5	-	5	-	ns	
f_{max}	maximum frequency	CP input; see Figure 7									
		$V_{CC} = 2.0$ V	6	17	-	5	-	4	-	MHz	
		$V_{CC} = 4.5$ V	30	51	-	24	-	20	-	MHz	
		$V_{CC} = 6.0$ V	35	61	-	28	-	24	-	MHz	
		$V_{CC} = 5.0$ V; $C_L = 15$ pF	-	56	-	-	-	-	-	MHz	
C_{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	[3]	-	35	-	-	-	-	pF	

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

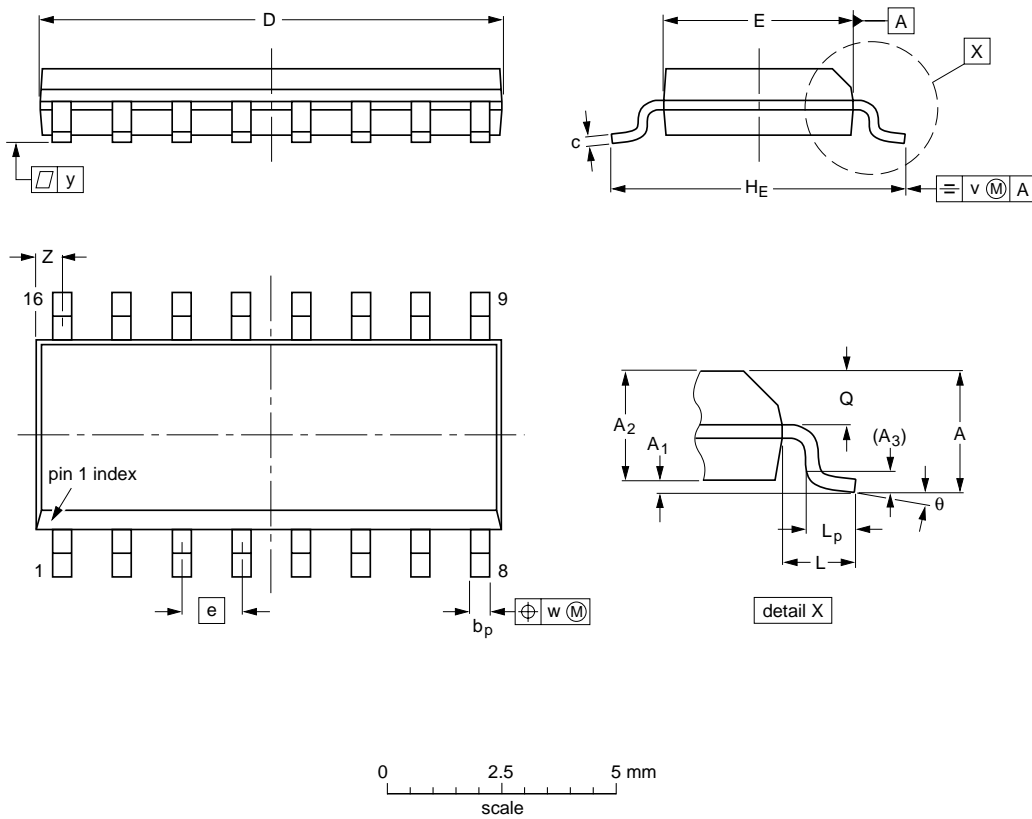
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION
	IEC	JEDEC	JEITA		
SOT38-4					

Fig 13. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION
	IEC	JEDEC	JEITA		
SOT109-1	076E07	MS-012			

Fig 14. Package outline SOT109-1 (SO16)